# N-Channel 60-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

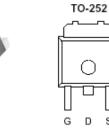
### **Typical Applications:**

- Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

PRODUCT SUMMARY				
VDS (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
60	65 @ V <sub>GS</sub> = 10V	23		
	78 @ V <sub>GS</sub> = 4.5V	21		

in





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G	D	S
То	p Vie	w

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			60	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	v	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	23	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	90	~	
Continuous Source Current (Diode Conduction) <sup>a</sup>		ا <sub>s</sub>	30	А	
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	50	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ extsf{ heta}JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	C/ VV		

Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- Pulse width limited by maximum junction temperature b.

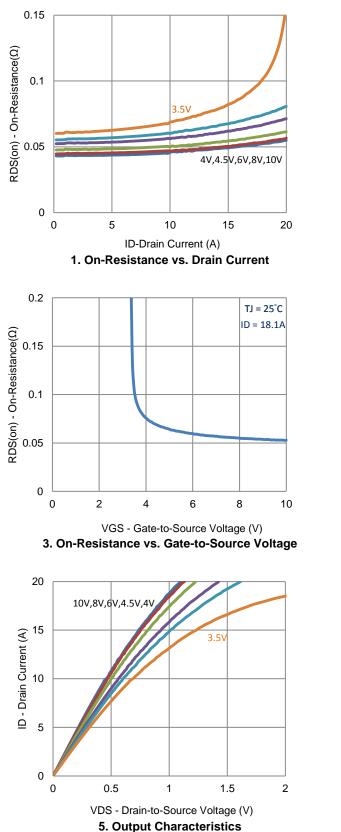
# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
	IDSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	= 55°C 25		25	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	35			А	
	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 18.1 \text{ A}$			65		
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS}$ = 4.5 V, I <sub>D</sub> = 14.5 A			78	mΩ	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 18.1 \text{ A}$		15		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.95		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		3.6			
Gate-Source Charge	$Q_gs$	$V_{DS} = 30$ V, $V_{GS} = 4.3$ V, $I_{D} = 18.1$ A		1.3		nC	
Gate-Drain Charge	$Q_gd$	ID = 10.1 A		1.7			
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 30 V, R <sub>I</sub> = 1.7 Ω,		3			
Rise Time	t <sub>r</sub>	$V_{DS} = 30$ V, $K_L = 1.7 \Omega_2$ , $I_D = 18.1 \text{ A}$ ,		4		20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		17		ns	
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$		5			
Input Capacitance	C <sub>iss</sub>			405			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		61		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			33			

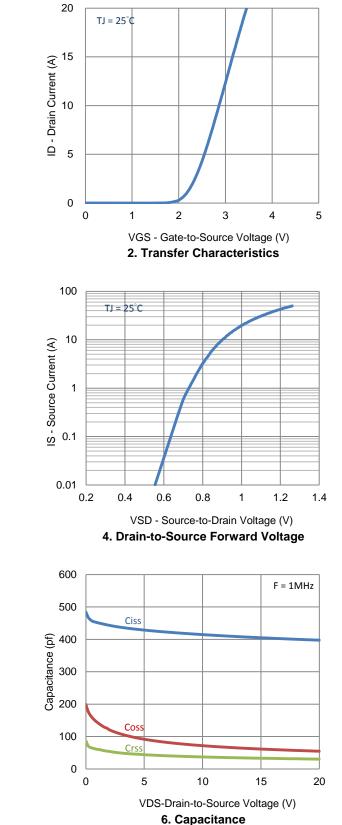
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

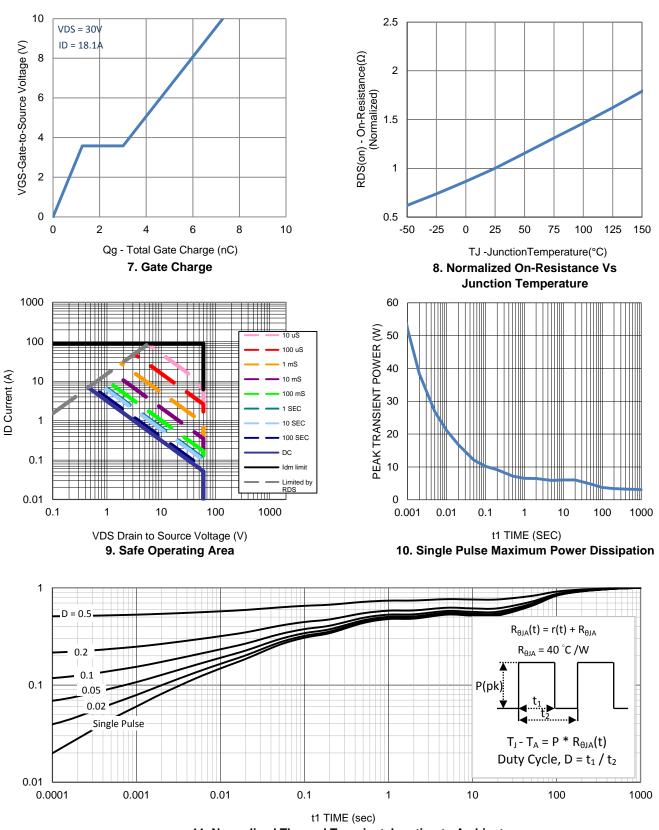
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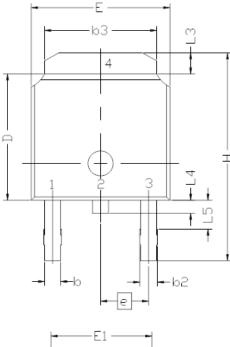
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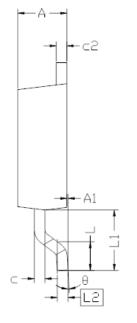


### **Typical Electrical Characteristics**

11. Normalized Thermal Transient Junction to Ambient

## **Package Information**





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<u>+                                     </u>	3 2 1
	SINGLE ROW <b>new</b>

SYMBOL	DIMENS: MIN	IUNAL H NOM	REQMTS MAX
	1 1211		
Ŀ	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		.743 RI	
L2	0.	.508 BS	C
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6.223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.	286 BS	C
A	2.20	2.30	2.38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5.30		
E1	4.40		
θ	0°		10°

#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.